Bulletin PD-20409 rev. C 01/07

International
IOR Rectifier

30BQ100PbF

SCHOTTKY RECTIFIER

3 Amp

$I_{F(AV)}$ = 3.0Amp
V_R = 100V

Major Ratings and Characteristics

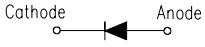
Characteristics	Values	Units
$I_{F(AV)}$ Rectangular waveform	3.0	A
V_{RRM}	100	V
I_{FSM} @t_p= 5 µs sine	800	A
V_F @3.0 Apk, T_J = 125°C	0.62	V
T_J range	- 55 to 175	°C

Description/ Features

The 30BQ100PbF surface-mount Schottky rectifier has been designed for applications requiring low forward drop and small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead-Free ("PbF" suffix)

Case Styles



SMC

Voltage Ratings

	Part number	30BQ100PbF
V_R	Max. DC Reverse Voltage (V)	100
V_{RWM}	Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

	Parameters	30BQ	Units	Conditions	
$I_{F(AV)}$	Max. Average Forward Current	3.0	A	50% duty cycle @ T_L = 148 °C, rectangular wave form	
		4.0		50% duty cycle @ T_L = 138 °C, rectangular wave form	
I_{FSM}	Max. Peak One Cycle Non-Repetitive	800	A	5µs Sine or 3µs Rect. pulse	Following any rated load condition and with rated V_{RRM} applied
	Surge Current	70		10ms Sine or 6ms Rect. pulse	
E_{AS}	Non Repetitive Avalanche Energy	3.0	mJ	T_J = 25 °C, I_{AS} = 1.0A, L = 6mH	
I_{AR}	Repetitive Avalanche Current	0.5	A	Current decaying linearly to zero in 1 µsec Frequency limited by T_J max. Va = 1.5 x Vr typical	

Electrical Specifications

	Parameters	30BQ	Units	Conditions	
V_{FM}	Max. Forward Voltage Drop (1)	0.79	V	@ 3A	T_J = 25 °C
		0.90	V	@ 6A	
		0.62	V	@ 3A	T_J = 125 °C
		0.70	V	@ 6A	
I_{RM}	Max. Reverse Leakage Current (1)	0.5	mA	T_J = 25 °C	V_R = rated V_R
		5.0	mA	T_J = 125 °C	
C_T	Max. Junction Capacitance	115	pF	V_R = 5V_{DC} (test signal range 100KHz to 1Mhz) 25°C	
L_S	Typical Series Inductance	3.0	nH	Measured lead to lead 5mm from package body	
dv/dt	Max. Voltage Rate of Change	10000	V/µs	(Rated V_R)	

(1) Pulse Width < 300µs, Duty Cycle < 2%

Thermal-Mechanical Specifications

	Parameters	30BQ	Units	Conditions
T_J	Max. Junction Temperature Range (*)	-55 to 175	°C	
T_{stg}	Max. Storage Temperature Range	-55 to 175	°C	
R_{thJL}	Max. Thermal Resistance Junction to Lead (**)	12	°C/W	DC operation
R_{thJA}	Max. Thermal Resistance Junction to Ambient	46	°C/W	DC operation
wt	Approximate Weight	0.24 (0 008)	g (oz.)	
	Case Style	SMC		Similar to DO-214AB
	Device Marking	IR3J		

(*) $\frac{dPtot}{dTj} < \frac{1}{Rth(j\text{-}a)}$ thermal runaway condition for a diode on its own heatsink

(**) Mounted 1 inch square PCB

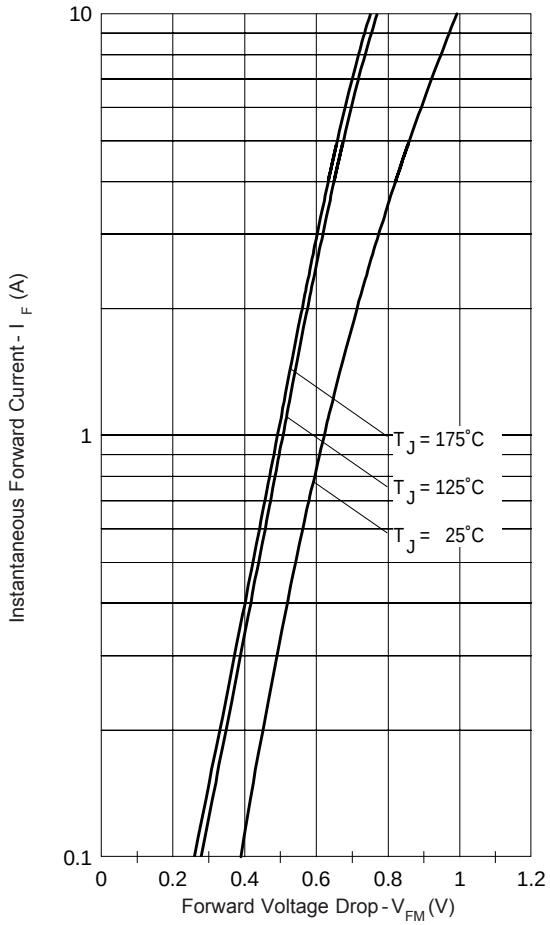


Fig. 1 - Max. Forward Voltage Drop Characteristics (Per Leg)

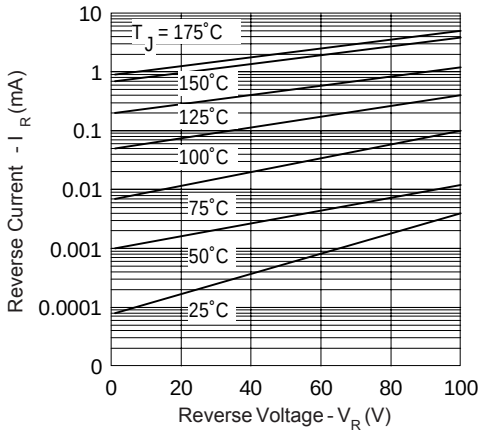


Fig. 2 - Typical Values Of Reverse Current Vs. Reverse Voltage (Per Leg)

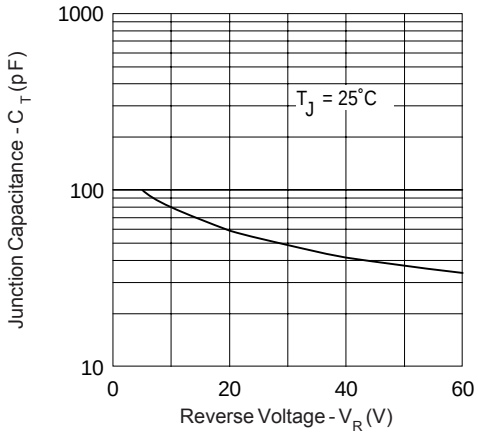


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage (Per Leg)

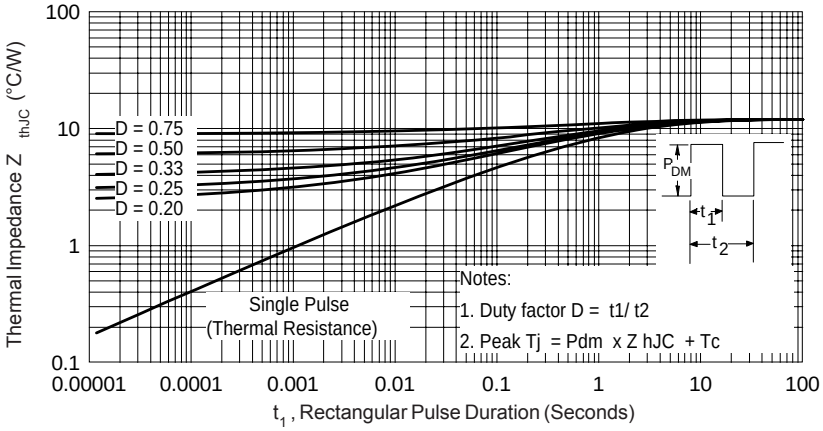


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics (Per Leg)

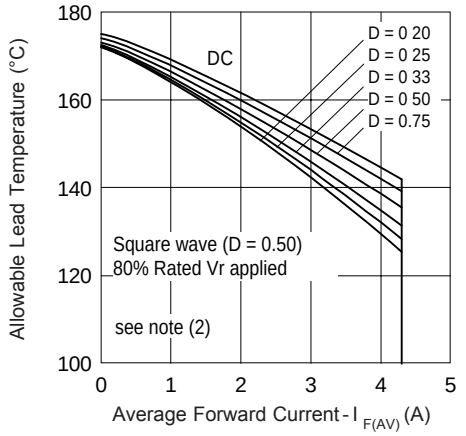


Fig. 4 - Maximum Average Forward Current
Vs. Allowable Lead Temperature

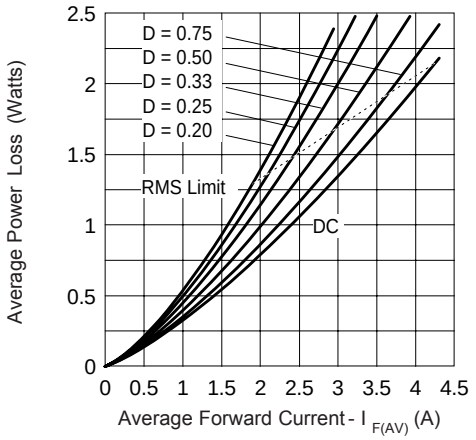


Fig. 5 - Maximum Average Forward Dissipation
Vs. Average Forward Current

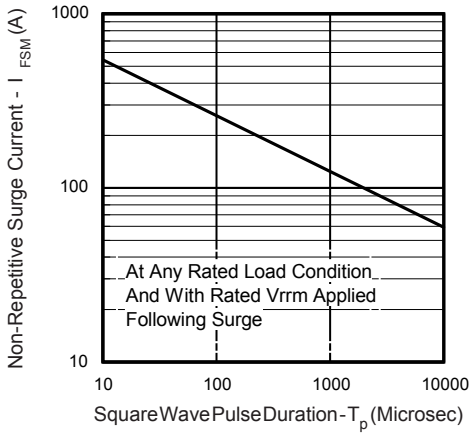
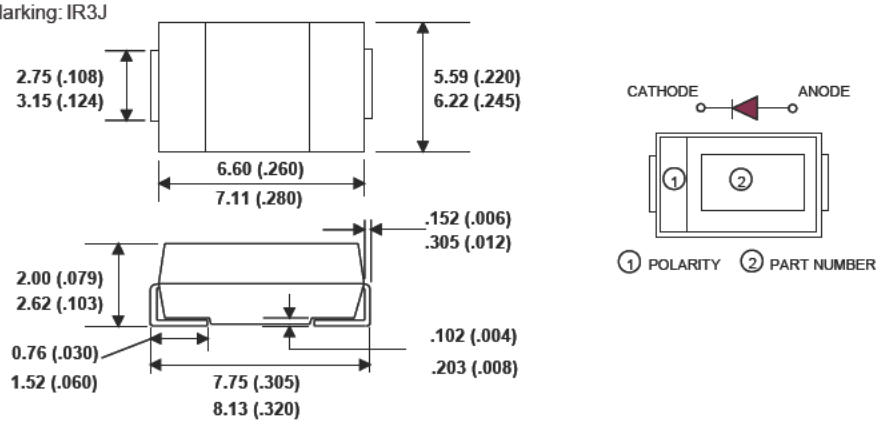


Fig. 6 - Maximum Peak Surge Forward Current Vs. Pulse Duration

(2) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = Forward Power Loss = $I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);
Pd_{REV} = Inverse Power Loss = $V_{R1} \times I_R (1 - D)$; $I_R @ V_{R1}$ = 80% rated V_R

Outline Table

Device Marking: IR3J



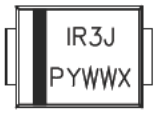
Outline SMC

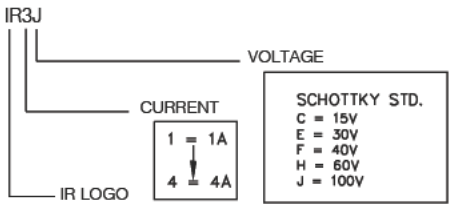
Dimensions in millimeters and (inches)

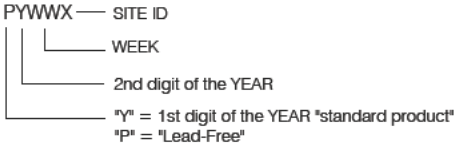
For recommended footprint and soldering techniques refer to application note #AN-994

Marking & Identification

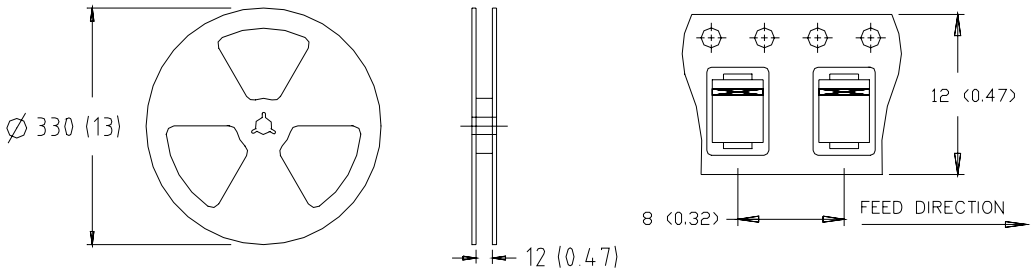
Each device has 2 rows for identification. The first row designates the device as manufactured by International Rectifier, indicated by the letters "IR", and the Part Number (indicates the current, the voltage rating and Schottky Generation). The second row indicates the year, the week of manufacturing and the Site ID.







Tape & Reel Information



Dimensions in millimetres and (inches)

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30BQ100
*****************************************
* SPICE Model Diode                     *
*****************************************
.SUBCKT 30BQ100 ANO CAT
D1 ANO 1 CAT
*Define diode model
.MODEL DMOD D (IS=100N, N=1.34718, BV=120, RS=40.3878M, CJO=158.574P, VJ=3.61795,
M=526.488M, EG=1.11, XTI=2, RL=25.6436MEG).


********************************************************************************


.ENDS  30BQ100


Thermal Model Subcircuit
.SUBCKT 30BQ100  5 1

CTHERM1       5    4      6.42E-01
CTHERM2       4    3      1.03E+01
CTHERM3       3    2      1.66E+02
CTHERM4       2    1      6.78E+03

RTHERM1       5    4      3.34E+00
RTHERM2       4    3      4.97E+00
RTHERM1       3    2      2.84E+00
RTHERM1       2    1      7.75E-01



.ENDS 30BQ100
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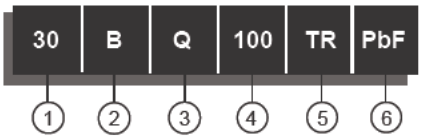
Ordering Information Table

Device Code



1 - Current Rating
2 - B = Single Lead Diode
3 - Q = Schottky Q Series
4 - Voltage Rating (100 = 100V)
5 - • none = Box (1000 pieces)
    • TR = Tape & Reel (3000 pieces)
6 - • none = Standard Production
    • PbF = Lead-Free

Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level and Lead-Free.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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